

Linear Systems replaces discontinued Siliconix J212

The LSJ212 is a n-channel JFET General Purpose amplifier with low noise and low leakage.

The SOT-23 package is well suited for cost sensitive applications and mass production.

(See Packaging Information).

LSJ212 Benefits:

- High gain
- Low Leakage
- Low Noise

LSJ212 Applications:

- General Purpose Amplifiers
- UHV / VHF Amplifiers
- Mixers
- Oscillators

FEATURES	
DIRECT REPLACEMENT FOR SILICONIX J212	
HIGH GAIN	$g_{fs} = 7000 \mu\text{mho MIN}$
HIGH INPUT IMPEDANCE	$I_{GSS} = 100\text{pA max}$
LOW INPUT CAPACITANCE	$C_{iss} = 5\text{pF}$
ABSOLUTE MAXIMUM RATINGS @ 25°C (unless otherwise noted)	
Maximum Temperatures	
Storage Temperature	-55°C to +150°C
Operating Junction Temperature	-55°C to +135°C
Maximum Power Dissipation	
Continuous Power Dissipation	360mW
Derating over temperature	3.27 mW/°C
MAXIMUM CURRENT	
Gate Current (Note 1)	10mA
MAXIMUM VOLTAGES	
Gate to Drain Voltage or Gate to Source Voltage	-25V

LSJ212 ELECTRICAL CHARACTERISTICS @ 25°C (unless otherwise noted)

SYMBOL	CHARACTERISTIC	MIN	TYP.	MAX	UNITS	CONDITIONS
BV_{GSS}	Gate to Source Breakdown Voltage	-25	--	--	V	$V_{DS} = 0V, I_G = -1\mu A$
$V_{GS(off)}$	Gate to Source Cutoff Voltage	-4	--	-6	V	$V_{DS} = 15V, I_D = 1nA$
I_{DSS}	Drain to Source Saturation Current (Note 2)	15	--	40	mA	$V_{DS} = 15V, V_{GS} = 0V$
I_{GSS}	Gate Reverse Current (Note 3)	--	--	-100	pA	$V_{DS} = 0V, V_{GS} = -15V$
I_G	Gate Operating Current (Note 3)	--	-10	--	pA	$V_{DS} = 10V, I_D = 1mA$
$r_{DS(on)}$	Drain to Source On Resistance	--	--	50	Ω	$I_G = 1mA, V_{DS} = 0V$

LSJ212 DYNAMIC ELECTRICAL CHARACTERISTICS @ 25°C (unless otherwise noted)

SYMBOL	CHARACTERISTIC	MIN	TYP.	MAX	UNITS	CONDITIONS
g_{fs}	Forward Transconductance	7000	--	12000	μmho	$V_{DS} = 15V, V_{GS} = 0V, f = 1\text{kHz}$
g_{os}	Output Conductance	--	--	200	μmho	$V_{DS} = 15V, V_{GS} = 0V, f = 1\text{kHz}$
C_{iss}	Input Capacitance	--	4	--	pF	$V_{DS} = 15V, V_{GS} = 0V, f = 1\text{MHz}$
C_{rss}	Reverse Transfer Capacitance	--	1	--	pF	$V_{DS} = 15V, V_{GS} = 0V, f = 1\text{MHz}$
e_n	Equivalent Noise Voltage	--	10	--	nV/√Hz	$V_{DS} = 15V, V_{GS} = 0V, f = 1\text{kHz}$

LSJ212 SWITCHING CHARACTERISTICS @ 25°C (unless otherwise noted)

SYMBOL	CHARACTERISTIC	UNITS	CONDITIONS
$t_{d(on)}$	Turn On Time	2	$V_{DD} = 10V$ $V_{GS(H)} = 0V$ See Switching Circuit
t_r	Turn On Rise Time	2	
$t_{d(off)}$	Turn Off Time	6	
t_f	Turn Off Fall Time	15	

Note 1 - Absolute maximum ratings are limiting values above which LSJ212 serviceability may be impaired.

Note 2 - Pulse test duration = 2ms

Note 3 - Approximately doubles for every 10°C increase in T_A

Micross Components Europe

Available Packages:

SOT-23 (Top View)



LSJ212 in SOT-23
LSJ212 in bare die.

Tel: +44 1603 788967
Email: chipcomponents@micross.com
Web: <http://www.micross.com/distribution>

Please contact Micross for full package and die dimensions

